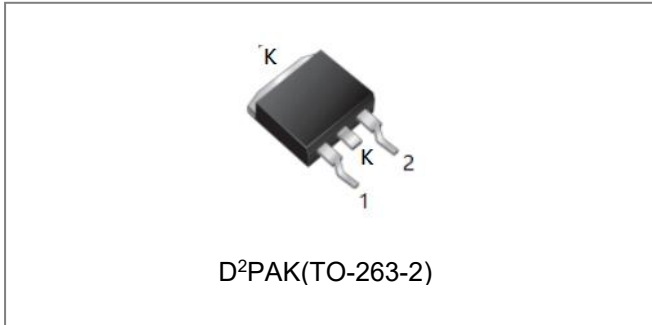


S4D15120G

15A 1200V SiC POWER SCHOTTKY RECTIFIER



Description

S4D15120G is single SiC Schottky rectifier packaged in D²PAK(TO-263-2) case. The device is a high voltage Schottky rectifier that has very low total conduction losses and very stable switching characteristics over temperature extremes. The S4D15120G is ideal for energy sensitive, high frequency applications in challenging environments.

Circuit Diagram



Features

- 175°C T_J operation
- Ultra-low switching loss
- Switching speeds independent of operating temperature
- Low total conduction losses
- High forward surge current capability
- High package isolation voltage
- Terminals finish: 100% Pure Tin
- “-A” is an AEC-Q101 qualified device
- Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional electrical and life testing can be performed upon request

Applications

- Alternative energy inverters
- Power Factor Correction (PFC)
- Free-Wheeling diodes
- Switching supply output rectification
- Reverse polarity protection

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage	V _{RRM}	-	1200	V
Working Peak Reverse Voltage	V _{RWM}			
DC Blocking Voltage	V _R			
Average Rectified Forward Current	I _{F(AV)1}	T _c =25°C	46	A
	I _{F(AV)2}	T _c =150°C	15	A
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	10ms, Half Sine pulse, T _c = 25 °C	130	A
Repetitive Peak Forward Surge Current	I _{FRM}	10ms, Half Sine pulse, T _c = 25 °C	68	A
Power Dissipation	P _{tot1}	T _c =25°C	178.6	W
	P _{tot2}	T _c =110°C	77.4	W

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop *	V _{F1}	@ 15A, Pulse, T _J = 25 °C	1.5	1.8	V
	V _{F2}	@ 15A, Pulse, T _J = 175 °C	2.2	3.0	V
Reverse Current *	I _{R1}	@V _R = rated V _R T _J = 25 °C	3	40	uA
	I _{R2}	@V _R = rated V _R T _J = 175 °C	10	50	uA
Junction Capacitance	C _T	V _R =0V, T _j =25°C, f=1MHz	990	-	pF
Reverse Recovery Charge	Q _c	I _F = 15A, di/dt = 200A/μs V _R = 800 V, T _J =25°C	76.32	-	nC
Capacitance Stored Energy	E _c	V _R = 800 V, T _J =25°C	39.24	-	μJ

* Pulse width < 300 μs, duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T _J	-	-55 to +175	°C
Storage Temperature	T _{stg}	-	-55 to +175	°C
Typical Thermal Resistance Junction to Case	R _{θJC}	DC operation	1.65	°C/W

Ordering Information

Device	Package	Shipping
S4D15120G	D ² PAK(TO-263-2)	800pcs / reel
S4D15120GTR	D ² PAK(TO-263-2)	800pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram


Where XXXXX is YYWWL

S3D = Device Type
 G = Package type
 15 = Forward Current (15A)
 120 = Reverse Voltage (1200V)
 SSG = SSG
 YY = Year
 WW = Week
 L = Lot Number

Cautions: Molding resin
 Epoxy resin UL:94V-0

Ratings and Characteristics Curves

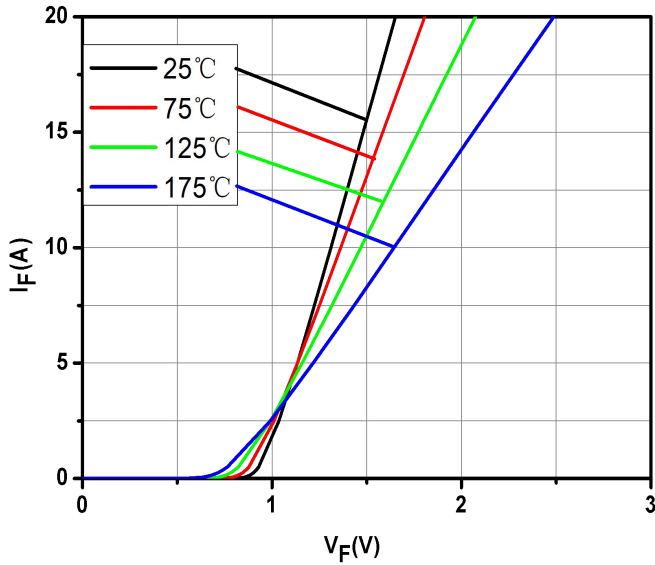


Fig.1-Typical Forward Voltage Characteristics

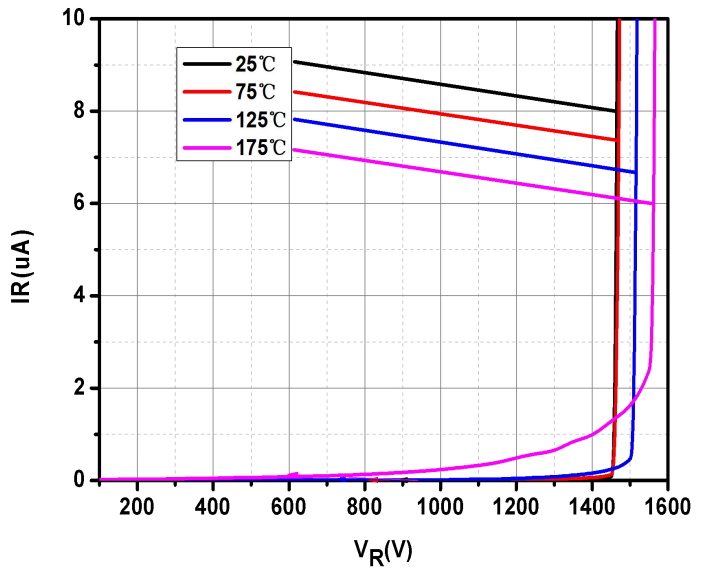


Fig.2-Typical Reverse Characteristics

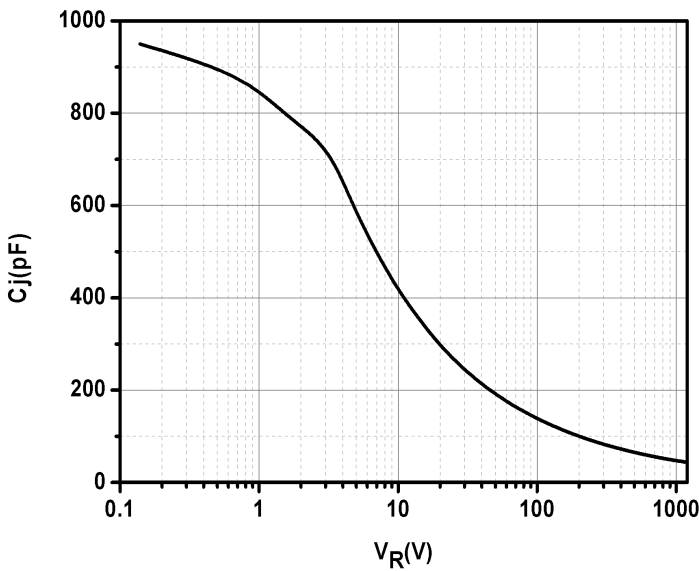


Fig.3-Capacitance vs. Reverse Voltage

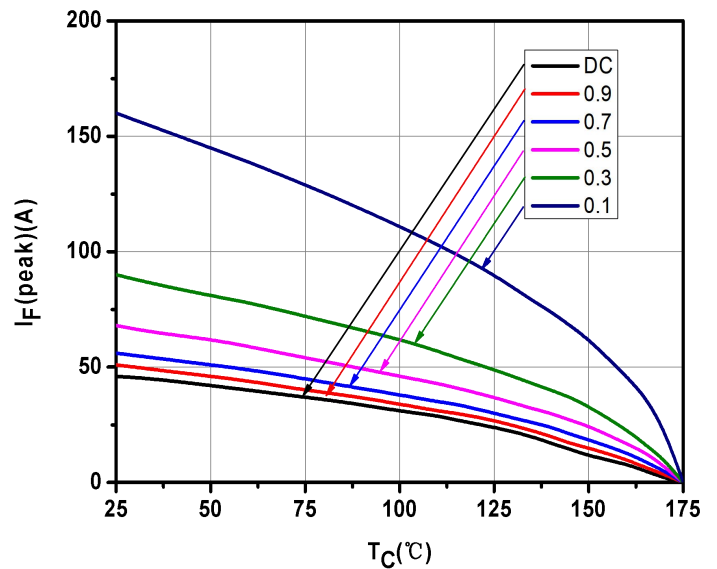


Fig.4-Current Derating

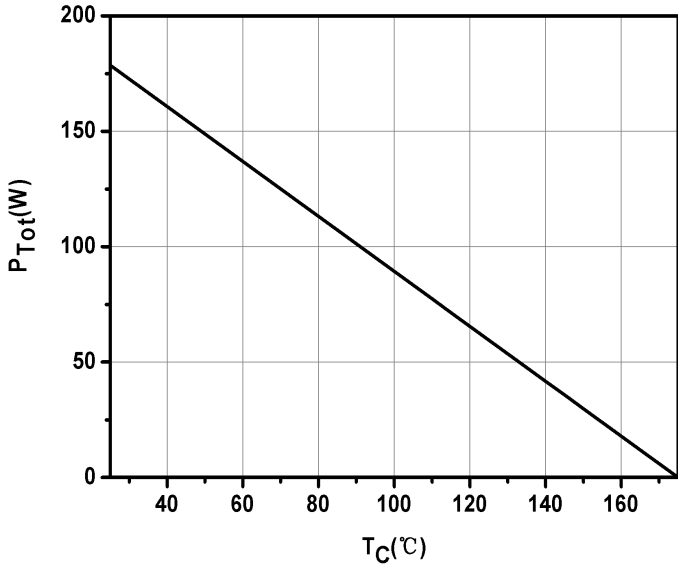


Fig.5-Power Derating

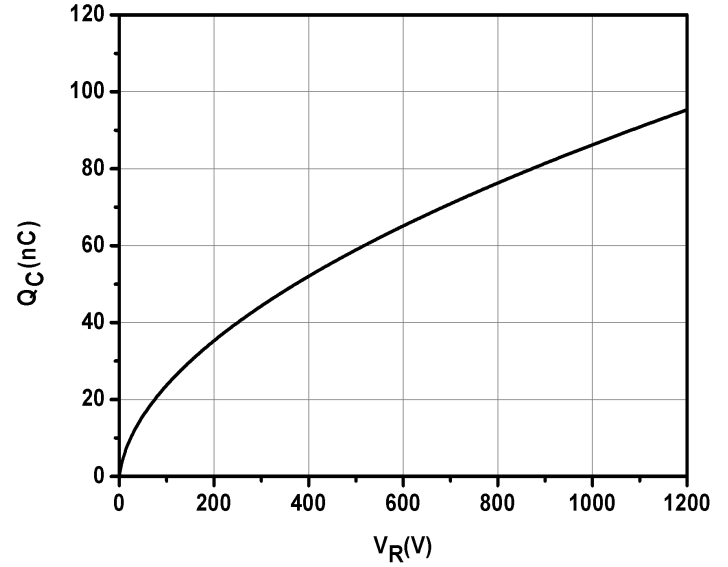


Fig.6-Total Capacitance Charge vs. Reverse Voltage

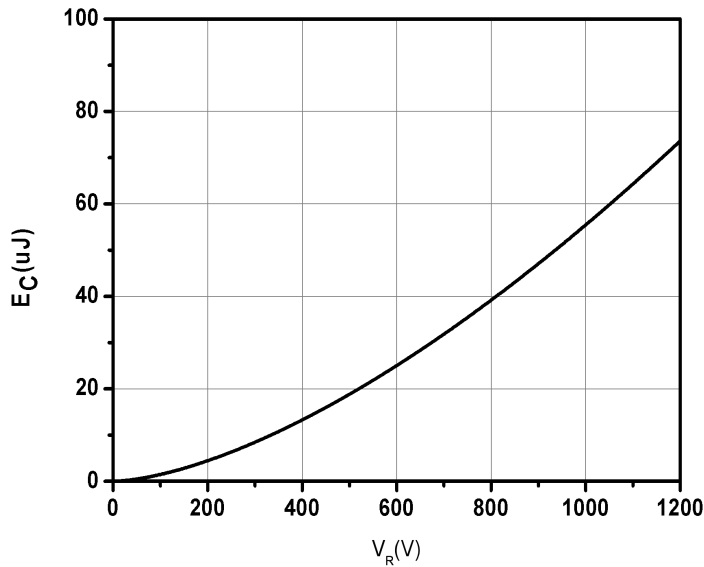
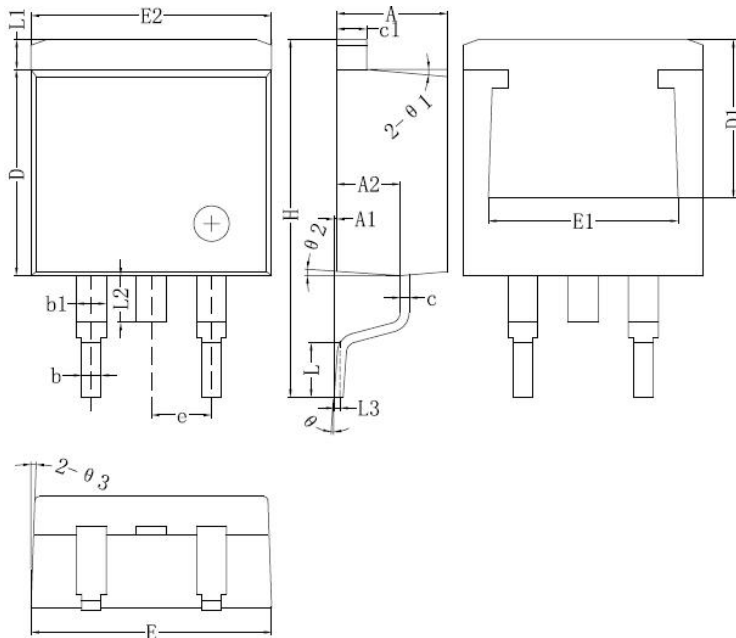


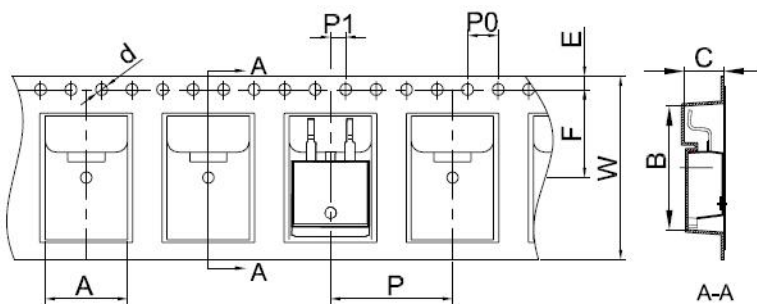
Fig.7-Capacitance Stored Energy

Mechanical Dimensions D²PAK(TO-263-2)



Symbol	Dimensions in millimeters	
	Min.	Max.
A	4.06	4.83
A1	0	0.26
b	0.51	0.99
b1	1.14	1.78
c	0.31	0.74
c1	1.14	1.65
D	8.38	8.65
D1	6.86	
E1	6.22	
E2	9.65	10.67
e	2.54BSC	
H	14.60	15.88
L	1.78	2.80
L1	-	1.68
L2	-	1.78
L3	0.255BSC	
Θ	0	8°

Carrier Tape & Reel Specification D²PAK(TO-263-2)



SYMBOL	Millimeters	
	Min.	Max.
A	10.70	10.90
B	16.03	16.23
C	5.11	5.31
d	1.45	1.65
E	1.65	1.85
F	11.40	11.60
P0	3.90	4.10
P	15.90	16.10
P1	1.90	2.10
W	23.90	24.30

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